

## Side illuminated monitor PIN PD

CPSX144S

### Features

- Side illuminated InGaAs/InP monitor photodiode
- Low dark current

### Applications

- Back facet monitoring of edge emitting lasers

### Absolute Maximum Ratings

Parameters	Symbol	Rating	Unit
Reverse voltage	$V_R$	20	V
Forward current	$I_F$	10	mA
Operating temperature range	$T_C$	-40 to +85	°C
Storage temperature range	$T_{STG}$	-40 to +125	°C

### Electro-Optical Characteristics

Parameters	Symbol	Test Condition	Min.	Typ.	Max.	Unit
Operating wavelength range	$\lambda$	-	1000	-	1640	nm
Dark current	$I_D$	$V_R=5.0V$	-	1	10	nA
Total capacitance	C	$f=1MHz, V_R=2.5V$	-	7	-	pF
Responsivity *	R	$V_R = 2.5V (@1550nm)$		0.7		A/W

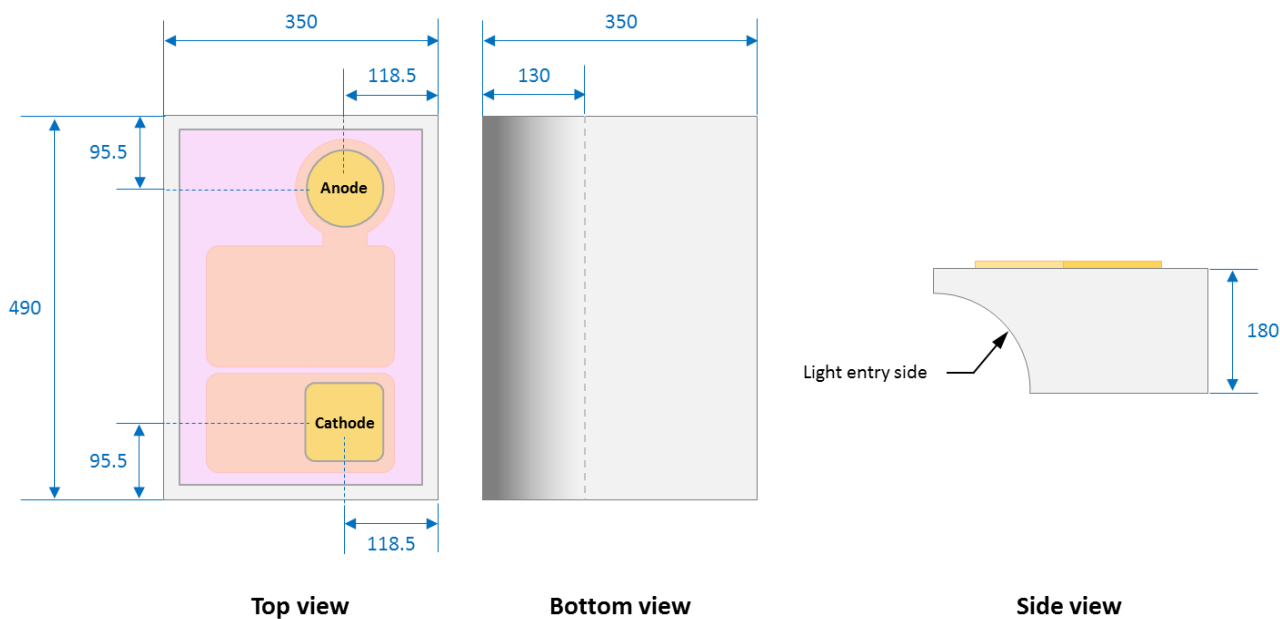
\* Coupling efficiency : 100%

### Dimensions

Parameters	Symbol	Size	Unit
Active area	-	144 x 233	$\mu m^2$
PD Chip size	$S_C$	350 x 490	$\mu m^2$
Chip thickness	T	$180 \pm 15$	$\mu m$
Edge Facet Depth	$D_D$	$130 \pm 20$	$\mu m$
Edge Facet Width	$D_W$	$130 \pm 20$	$\mu m$
Bonding pad	Anode	-	100
	Cathode	-	100 x 100

※ There is no AR coating on the light entry side.

# Preliminary datasheet



Unit :  $\mu\text{m}$

## Precaution to use

The CPSX144S is sensitive to electrostatic discharge (ESD) and should be handled with appropriate caution. Please use standard ESD protective equipment when handling this product.

## Ordering information

CPSX144S

Specifications described here are subject to change without notice



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